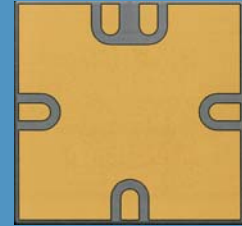


SURFACE MOUNT HIGH FREQUENCY, ACTIVE RF SWITCH SPDT



SERIES	SWITCH TYPE
InP1012	Solid State, InP-HEMT RF Switch

DESCRIPTION

The InP1012-30 is a highly compact, reflective SPDT Active RF switch, manufactured using Teledyne's high-speed, low-loss InP HEMT process. The switch die is packaged in a low-loss, surface mount package, with a small form factor: 3mm (L) × 3mm (W) × 1mm (H). It supports a wide frequency range from DC to 30 GHz, and delivers low insertion loss, fast switching time, and good isolation—making this switch ideal for test and measurement, microwave communications, and radar applications. The InP1012-30 can also tolerate up to 100 krad of radiation, allowing it to be used in space applications.

The InP1012-30 features:

- Broad frequency bandwidth, greater than 30 GHz
- Small form factor, 3mm X 3mm X 1mm
- Low insertion loss
- Very High linearity
- Wide operating temperature
- Radiation tolerant up to 100 krad
- Very fast switching time of less than 100 ns
- RoHS Compliant

The following unique construction features and manufacturing techniques provide excellent robustness to environmental extremes and overall high reliability:

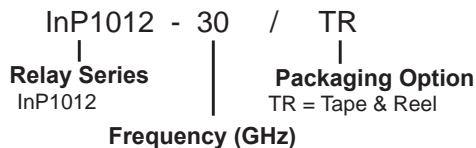
- Monolithic solid-state switch with no mechanical wear
- Flip-chip packaging provides shock & vibration resistance
- ENEPIG surface finish for solder bonding
- Low loss package with organic overmold
- Test board with K-connectors can be provided



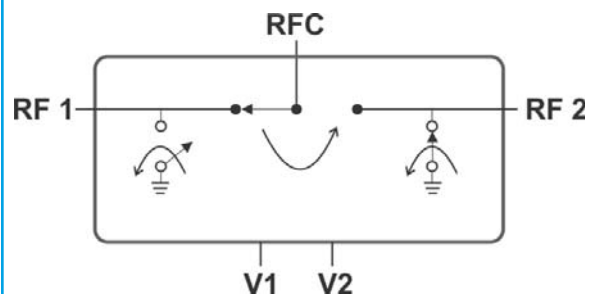
ENVIRONMENTAL AND PHYSICAL SPECIFICATIONS

Temperature (Ambient)	Storage	-65°C to +125°C
	Operating	-65°C to +125°C
Enclosure	Low-Loss Surface Mount Package	
ESD Sensitivity (HBM)	Class 1	
MSL Sensitivity	TBD	
Radiation Tolerance	100krads	

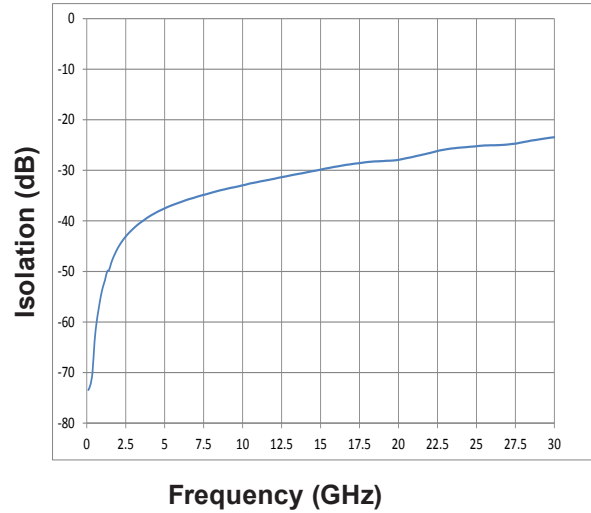
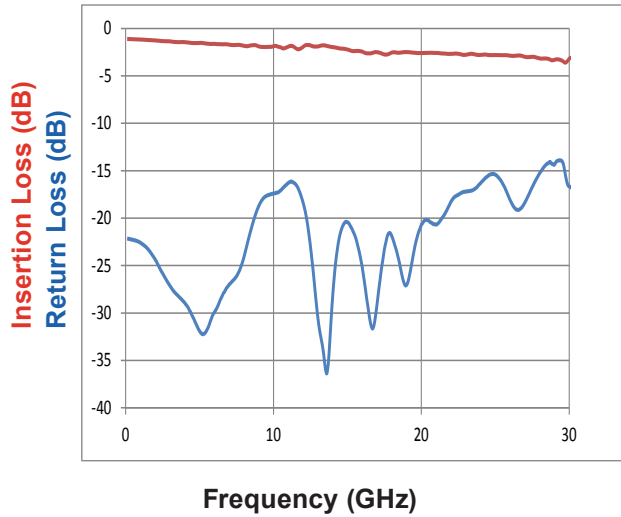
Teledyne Part Numbering System for InP1012



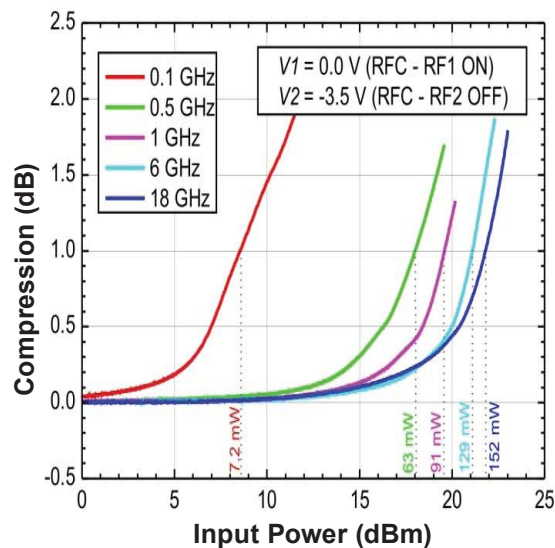
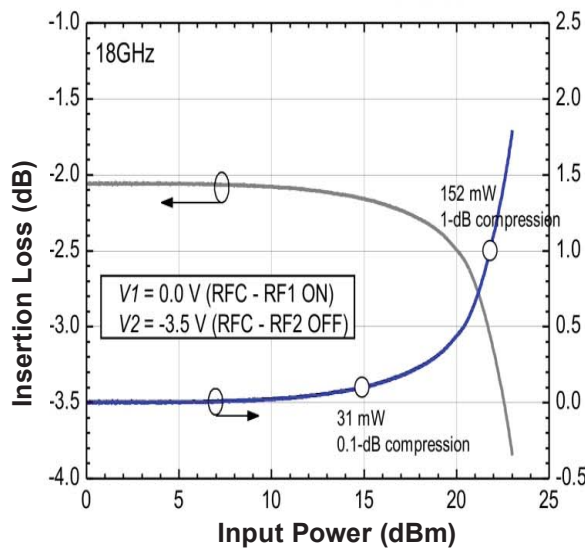
INTERNAL CONSTRUCTION



InP1012-30
TYPICAL RF CHARACTERISTICS (See RF Notes)



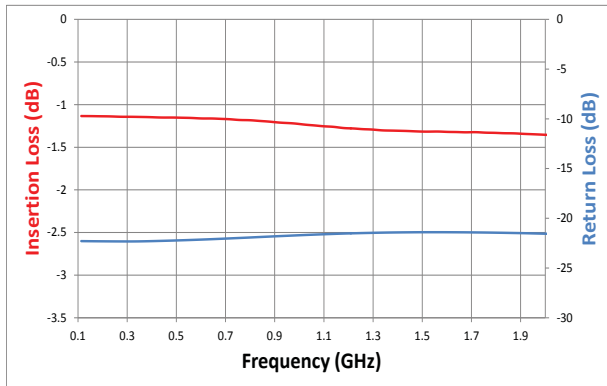
TYPICAL POWER HANDLING CHARACTERISTICS



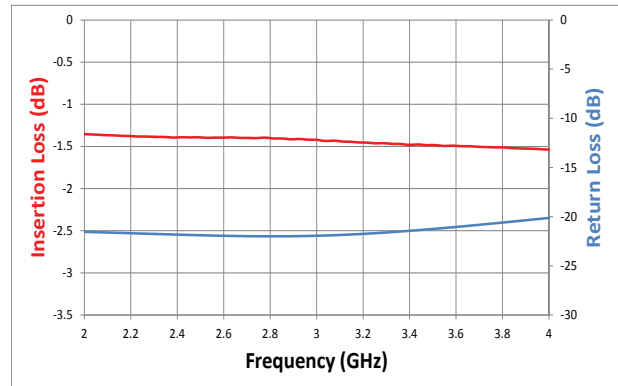
RF NOTES

- Test conditions:
 - Fixture: .020" RO4350B, ENIG plated, with 2.4mm connectors. (Trademark of Rogers Corporation.)
 - RF ground pad is soldered to PCB RF ground plane.
 - Room ambient temperature.
 - Terminals not tested were terminated with 50-ohm load.
 - Contact signal level: -10 dBm.
 - No. of test samples: 1.
- Data presented herein represents typical characteristics and is not intended for use as specification limits.

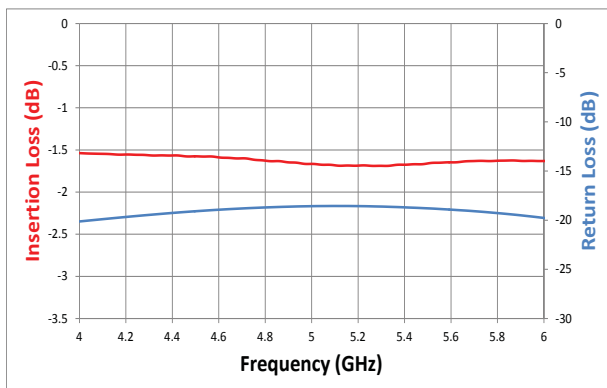
NARROWBAND INSERTION LOSS AND RETURN LOSS PLOTS



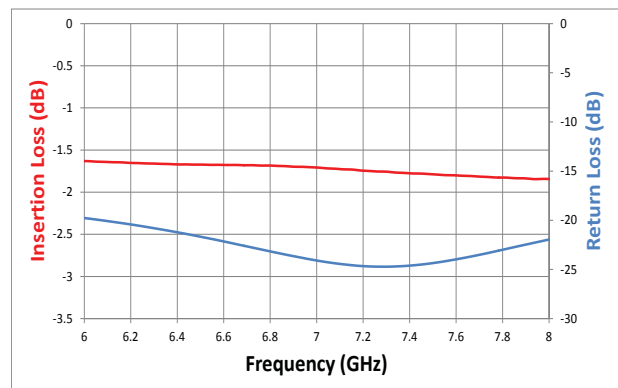
0.1 - 2 GHz



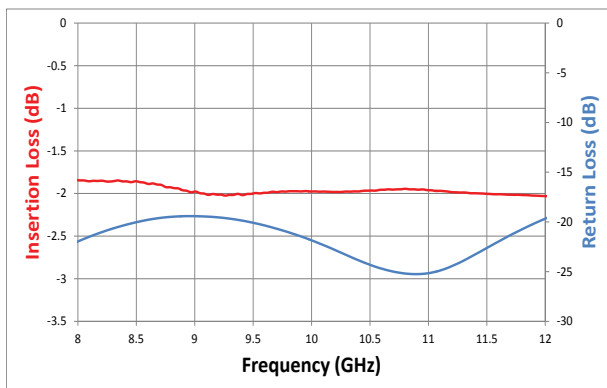
2 - 4 GHz



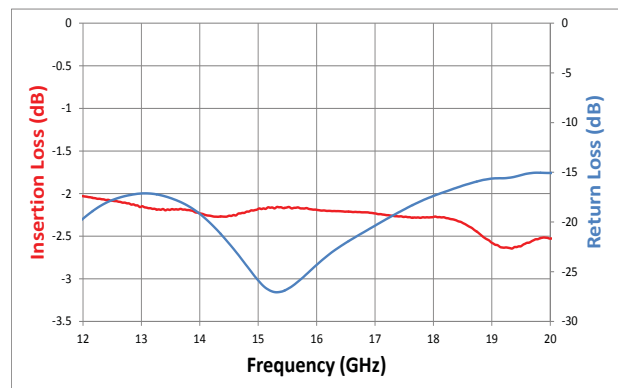
4 - 6 GHz



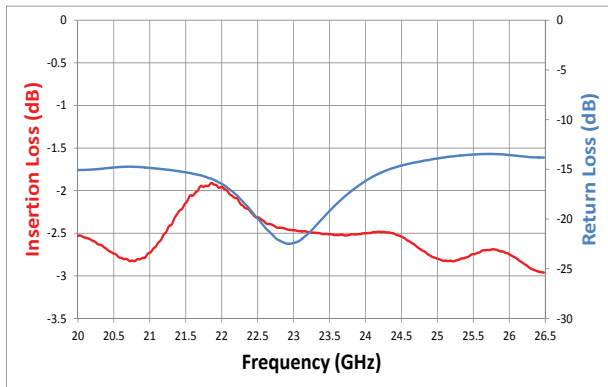
6 - 8 GHz



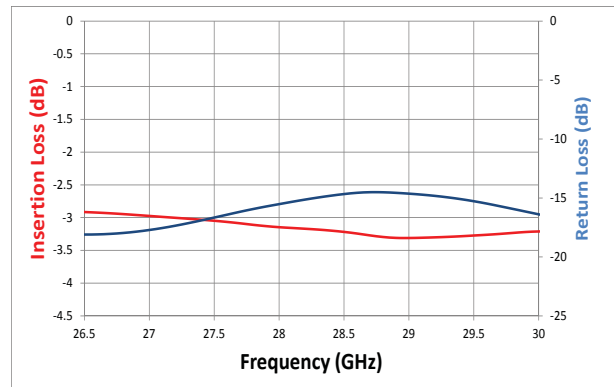
8 - 12 GHz



12 - 20 GHz

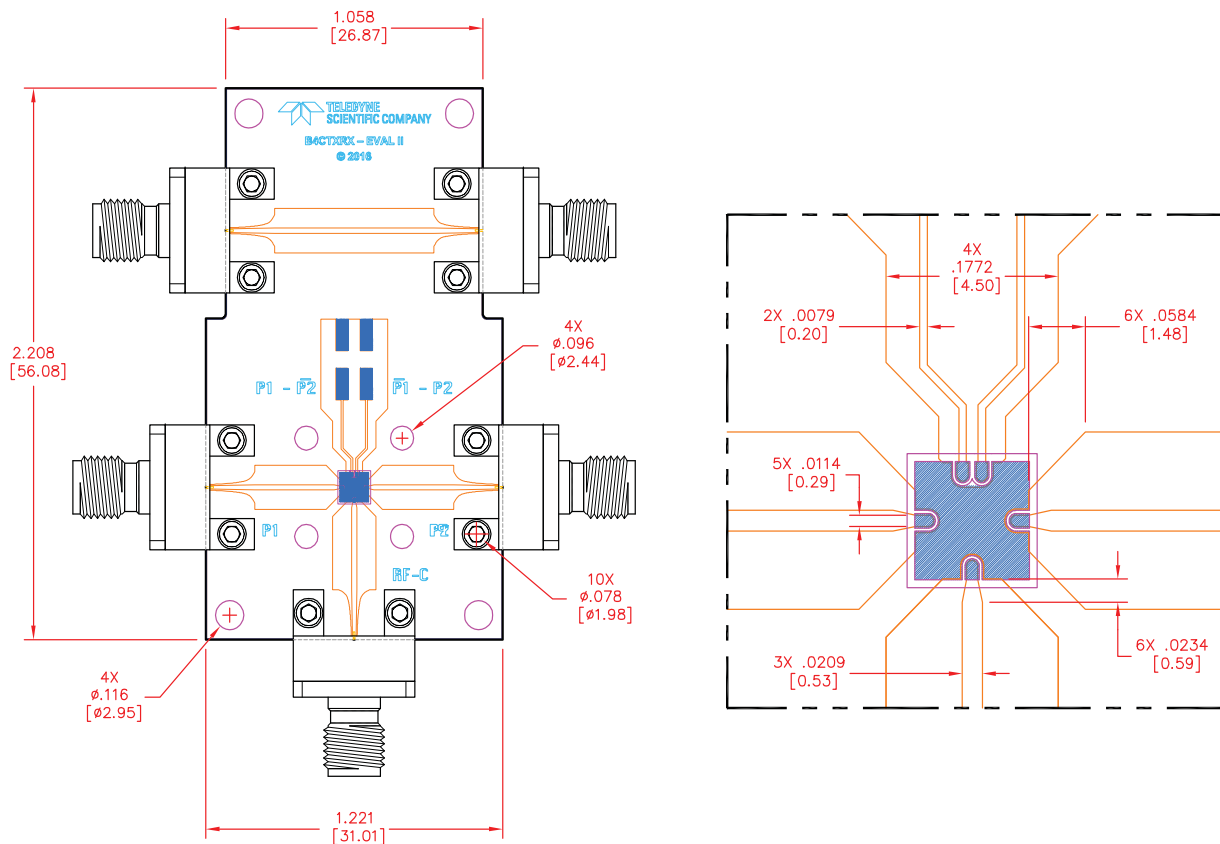


20 - 26.5 GHz



26.5 - 30 GHz

Evaluation Board



Note: RF and Signal Integrity measurements were made using the custom-built test board shown above .
Fixture: .020" RO4350B, ENIG plated, with 2.92mm connectors (Trademark of Rogers Corporation.)
RF ground pad is soldered to PCB RF ground plane.

To order the Evaluation Board, please use the following part number:

InP1012 - 30 / K
 | |
 Relay Series Evaluation Board
 InP1012
 | |
 Frequency (GHz)

TYPICAL ELECTRICAL SPECIFICATIONS (@25°C, V1 = ON, V2 = OFF OR V1 = OFF, V2 = ON, Z_s = Z_L = 50 Ω)
OPERATING FREQUENCY: DC - 30GHz

Parameter/Condition	Path	Condition	Typical	Unit
Insertion Loss	RFC-RFX	DC (20mV - 200mV)*	2.0	dB
		10 kHz	0.9	dB
		100 MHz	1.2	dB
		2 GHz	1.4	dB
		4 GHz	1.5	dB
		6 GHz	1.6	dB
		8 GHz	1.7	dB
		12 GHz	1.9	dB
		16 GHz	2.0	dB
		20 GHz	2.5	dB
Isolation	RFC-RFX	10 kHz	67	dB
		100 MHz	60	dB
		2 GHz	43	dB
		4 GHz	40	dB
		6 GHz	36	dB
		8 GHz	34	dB
		12 GHz	31	dB
		16 GHz	29	dB
		20 GHz	26	dB
		30 GHz	23	dB
Isolation	RF1-RF2	100 MHz	69	dB
		100 MHz - 26.5 GHz	32	dB
		26.5-30 GHz	27	dB
Return Loss (active port)	RFC-RFX	100 MHz	23	dB
		2 GHz	22	dB
		4 GHz	20	dB
		6 GHz	20	dB
		8 GHz	20	dB
		12 GHz	20	dB
		16 GHz	24	dB
		20 GHz	15	dB
		30 GHz	17	dB
Input 0.1dB compression point		100 MHz	3.1	dBm
		6 GHz	15.7	dBm
		18 GHz	14.9	dBm
Input 1dB compression point		100 MHz	8.6	dBm
		6 GHz	21.1	dBm
		18 GHz	21.8	dBm
Input 3 rd Order Intercept (IIP3)		10GHz	37.5	dBm

* Insertion loss increases with a higher DC offset, up to the 2.5Vdc Max.

GENERAL ELECTRICAL SPECIFICATIONS (@25°C)

Contact Arrangement	1 Form C (SPDT)
Rated Duty	Continuous
Operating Power	1-2 mW
Switching Time	60-100 ns

Note: Use DC blocking capacitors at RF ports.

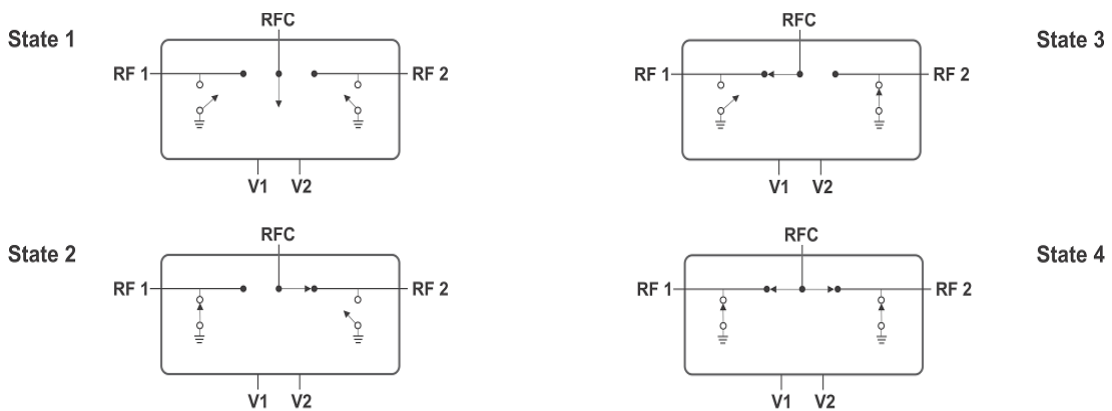
RECOMMENDED OPERATING CONDITIONS

Parameter	MIN	TYPICAL	MAX	UNIT
Control ON (V1,V2)	-0.3	0	+0.3	V
Control OFF (V1,V2)	-2.0	-2.5	-3.0	V
Control Current		200	700	μA

Note: Operation between -0.3V and -2.0V is not recommended.

SWITCH STATES

V1	V2	RF1	RF2	STATE
-2.5V	-2.5V	OFF	OFF	1
-2.5V	0V	OFF	ON	2
0V	-2.5V	ON	OFF	3
0V	0V	ON	ON	4

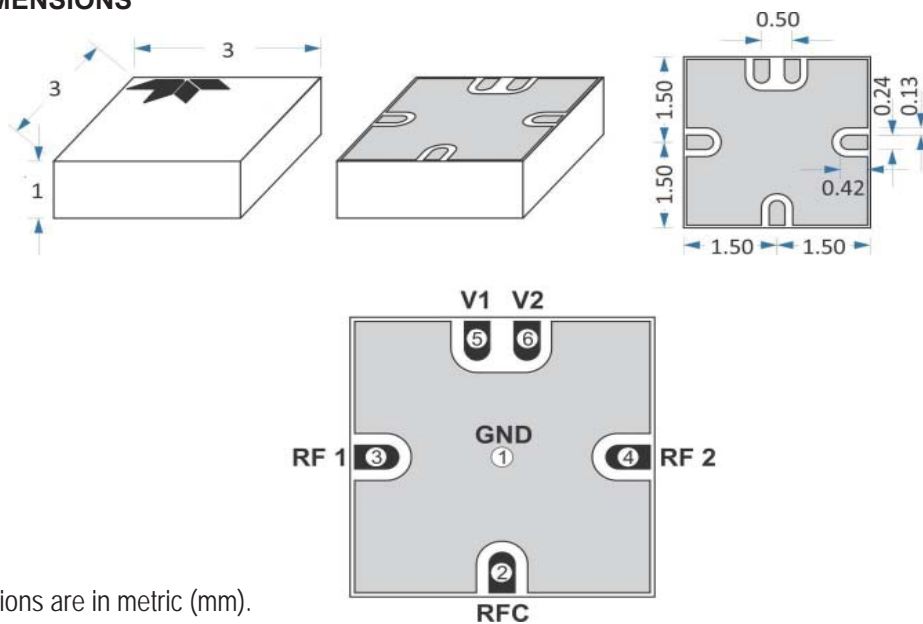


ABSOLUTE RATINGS

Parameter/Condition	MIN	MAX	UNIT
Control Voltage (V1,V2)	-3.0	+0.3	V
RF Input Power P1.0 dB (RFC-RFX, 50Ω)		8.6 @ 100 MHz 21.1 @ 6 GHz 21.8 @ 18 GHz	dBm dBm dBm
RF Contact Maximum DC Offset		2.5	V
Maximum Junction Temperature*		+180 (est.)	°C
Storage Temperature Range*	-65	+180 (est.)	°C

*InP die: 200°C for 30hours, BCB cure temperature: 250°C for 1hour, PbSn solder reflow temperature: 250°C for 1min, Pb37/Sn63 solder melting point: 183°C, MEG-TRON 6 substrate: 260°C, Sumitomo G770 epoxy overmold: 260°C

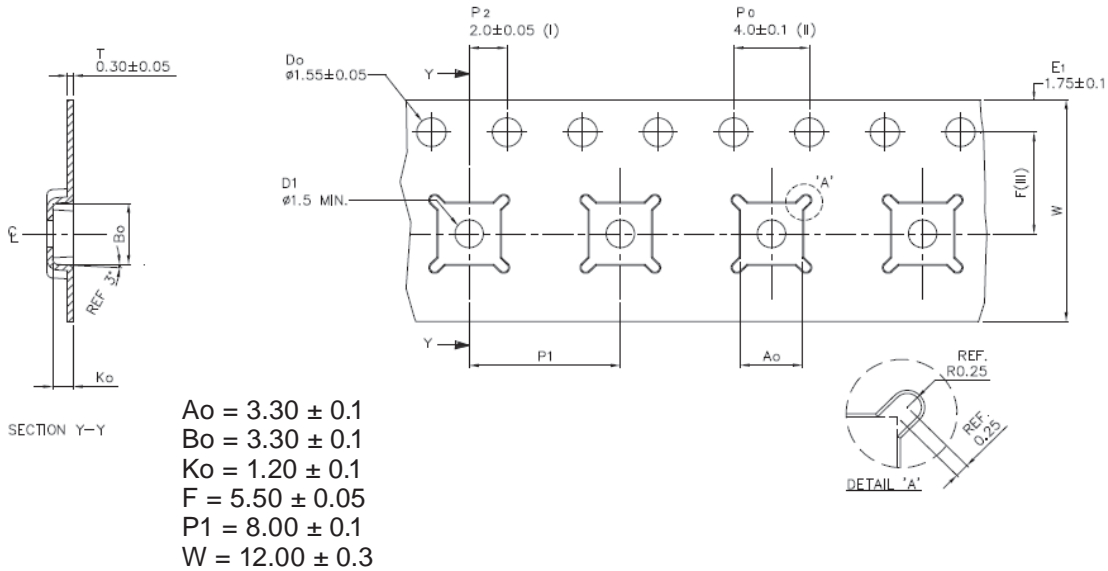
InP1012-30
OUTLINE DIMENSIONS



Note: Dimensions are in metric (mm).

Pad No.	Pad Name	Description
1	GND	Ground
2	RFC	RF Common Port
3	RF1	RF Port 1
4	RF2	RF Port 2
5	V1	Control Input 1
6	V2	Control Input 2

TAPE AND REEL PACKAGING OPTIONS



Notes:

- 1) Cumulative Tolerance for 10 Sprocket Holes $\pm 0.2\text{mm}$
- 2) A_o and B_o measured from a plane 0.3mm above bottom of pocket
- 3) Pocket position relative to sprocket hole and true position of pocket
- 4) Tape Engineered to comply with ANSI/EIA 481 B (July 2002)
- 5) Material does not contain heavy metals
- 6) Camber in compliance with ANSI/EIA 481 B (July 2002)

DIE INFORMATION

PARAMETER	MIN	TYP	MAX	UNIT	TEST CONDITION
Die Size, Singulated (x,y)	820 x 950	830 x 960	840 x 970	μm	Including excess InP, maximum tolerance = $\pm 10 \mu\text{m}$
Wafer Thickness	615	625	635	μm	
Bump Pitch	150			μm	
Bump Height	50	60	70	μm	
Bump Diameter		79		μm	
UBM Diameter	65	69	74	μm	

Contact factory for die RF performance and additional information.

Handling Guidelines for Active RF Switches (InP Series)

1. Do not drop, throw, or in any way mishandle individual switches or cartons containing switches.
2. Store switches in a humidity-controlled, shock- and vibration-free environment. Storage temperature range limits are -65°C to $+125^{\circ}\text{C}$, however, when possible, switches should be stored in an ambient environment.
3. Do not expose switches to humid condition such that condensation may be formed due to sudden drop in temperature. Switches shall be stored in condensation free condition.
4. Do not stack heavy objects directly onto switches.
5. Active RF switches shall be treated as Electrostatic Discharge (ESD) sensitive and shall be handled accordingly. Always work in ESD protected station and wear wrist strap before handling the device.
6. When removing switches from packs, do so with extreme care. Do not allow the switches to fall onto any hard surface during unpacking. Do not “pour” the switches from the packing. Do not allow switches to fall onto the floor.
7. When transferring switches to a production area after unpacking, do so only in a suitable container, transport the devices in anti-static container, taking care not to drop the switches into the container, or to drop, throw or mishandle the container in any way.
8. For either metal-cover switches that are hermetically sealed or plastic switches that are not hermetically sealed, any damage to the casing, leads, or connector may compromise the relay’s performance and reliability.
9. Never subject switches to ultrasonic cleaning environment.
10. Do not submerge plastic switches, which are not hermetically sealed, in cleaning solution or spray aqueous cleaning solution directly onto switches.
11. For plastic switches, which are not hermetically sealed, switches should be baked before use. After bake, switches must be mounted within 8 hours. Switches must be baked again if this 8 hour time period is exceeded. The recommended bake profile is 125°C for 1 hour.
12. After the reflow/mounting process, switches should be baked again after cleaning, prior to a second reflow, or prior to conformal coating.
13. Unless otherwise specified, do not subject switches and relay terminals to reflow solder temperatures above 245°C , 6 seconds maximum. If hand soldering is used, the solder iron tip shall be properly grounded. Observe IPC J-HDBK- 001, paragraph 6.1.0.1 guidelines for heat sensitive components when hand soldering switches.
14. If reshipping product do so in original packaging from factory.
15. Switches should not be exposed to any process or environment that exceeds any limits within this guideline or any published specification that applies to the relay.